L Number	Hits	Search Text	DB	Time stamp
1	37	(semiconductor adj2 memory adj2 device) and (reference adj3 signal adj3	USPAT; EPO; JPO;	2004/03/05 16:24
2	3	generator) (semiconductor adj2 memory adj2 device) and (reference adj3 signal adj3 generator) and ((potential adj2	DERWENT USPAT; EPO; JPO; DERWENT	2004/03/05 16:26
3	4	regulator) or (set\$4 near3 potential)) (semiconductor adj2 memory adj2 device) and (reference adj3 signal adj3 generator) and ((potential near4	USPAT; EPO; JPO; DERWENT	2004/03/05 16:29
4	4	regulat\$4) or (set\$4 near3 potential)) (semiconductor adj2 memory adj2 device) and (reference adj3 signal adj3 generator) and ((potential near4 regulat\$4) or (set\$4 near3 potential) or	USPAT; EPO; JPO; DERWENT	2004/03/05 16:30
5	2143	<pre>(adjust\$5 near3 potential)) (semiconductor adj2 memory adj2 device) and ((potential near4 regulat\$4) or (set\$4 near3 potential) or (adjust\$5</pre>	USPAT; EPO; JPO; DERWENT	2004/03/05 16:30
6	439	near3 potential)) (semiconductor adj2 memory adj2 device) same ((potential near4 regulat\$4) or (set\$4 near3 potential) or (adjust\$5 near3 potential))	USPAT; EPO; JPO; DERWENT	2004/03/05 16:30
7	794	(semiconductor adj2 memory adj2 device) same ((potential adj3 regulat\$4) or (set\$4 adj3 potential) or (potential adj3 potential))	USPAT; EPO; JPO; DERWENT	2004/03/05 16:32
8	637	(semiconductor adj2 memory adj2 device) same ((potential adj3 regulat\$4) or (potential adj2 set\$4 adj2 up) or (potential adj3 potential))	USPAT; EPO; JPO; DERWENT	2004/03/05 16:32
9	200	(semiconductor adj2 memory adj2 device) near10 ((potential adj3 regulat\$4) or (potential adj2 set\$4 adj2 up) or (potential adj3 potential))	USPAT; EPO; JPO; DERWENT	2004/03/05 16:33
10	1140	(semiconductor adj2 memory adj2 device) and ((potential adj3 regulat\$4) or (potential adj2 set\$4 adj2 up) or (potential adj3 potential)) and (signal adj2 generat\$3)	USPAT; EPO; JPO; DERWENT	2004/03/05 16:34
11	20	(semiconductor adj2 memory adj2 device) and ((potential adj3 regulat\$4) or (potential adj2 set\$4 adj2 up) or (potential adj3 potential)) and (reference adj2 signal adj2 generat\$3)	USPAT; EPO; JPO; DERWENT	2004/03/05 16:34
12	19	(semiconductor adj2 memory adj2 device) and ((potential adj3 regulat\$4) or (potential adj2 set\$4 adj2 up) or (potential adj3 potential)) and (reference adj2 signal adj2 generat\$3)	USPAT; EPO; JPO; DERWENT	2004/03/05 16:49
13	1	and amplif\$5 reference adj2 potential adj2 set adj2 up adj2 circuit	USPAT; EPO; JPO;	2004/03/05
14	3	potential adj2 set adj2 up adj2 circuit	DERWENT USPAT; EPO; JPO; DERWENT	2004/03/05 16:53
15	27	potential adj2 regulating adj2 circuit	USPAT; EPO; JPO; DERWENT	2004/03/05 16:54
16	450	potential adj2 regulator	USPAT; EPO; JPO; DERWENT	2004/03/05 16:54
17	7	(potential adj2 regulator) same memory	USPAT; EPO; JPO; DERWENT	2004/03/05 16:57

			T I I C D D M -	2004/02/05
18	6312	potential near3 arrang\$5	USPAT;	2004/03/05
			EPO; JPO;	16:58
	Ì		DERWENT	
19	2714	potential adj3 arrang\$5	USPAT;	2004/03/05
1			EPO; JPO;	16:58
			DERWENT	
20	3234	(potential adj3 arrang\$5) or (potential	USPAT;	2004/03/05
}		adj2 set adj2 up)	EPO; JPO;	16:58
			DERWENT	
21	49	((potential adj3 arrang\$5) or (potential	USPAT;	2004/03/05
İ		adj2 set adj2 up)) same (semiconductor	EPO; JPO;	17:15
-		adj2 memory)	DERWENT	
22	4346		USPAT;	2004/03/05
			EPO; JPO;	17:16
			DERWENT	
23	233	conventional adj3 (ferroelectric adj2	USPAT;	2004/03/05
		memory)	EPO; JPO;	17:16
		•	DERWENT	
24	0	(conventional adj3 (ferroelectric adj2	USPAT;	2004/03/05
		memory)) and (potential adj2 set adj2 up	EPO; JPO;	17:18
		adj2 circuit)	DERWENT	
25	27		USPAT;	2004/03/05
20		memory)) and (potential adj4 circuit)	EPO; JPO;	17:33
		memory,, and (possitional day) criticals,	DERWENT	17.00
26	103	(ferroelectric adj2 memory) and	USPAT;	2004/03/05
		(potential adj4 circuit)	EPO; JPO;	17:33
		(potential auji circuit)	DERWENT	17.55
27	103	(ferroelectric adj2 memory) and	USPAT;	2004/03/05
- '	103	(potential adj4 circuit)	EPO; JPO;	17:33
		(potential adja cilcult)	DERWENT	17.55
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